EMH2412

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N-Channel Power MOSFET 24V, 6A, 27mΩ, Dual EMH8

Features

- · Low ON-resistance
- · Best suited for LiB charging and discharging switch
- · Common-drain type
- · 2.5V drive
- · Halogen free compliance
- · Protection diode in

Specifications

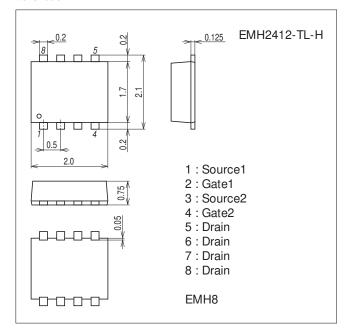
Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		24	V
Gate-to-Source Voltage	VGSS		±12	V
Drain Current (DC)	ID		6	Α
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	60	Α
Allowable Power Dissipation	PD	When mounted on ceramic substrate (900mm ² ×0.8mm) 1unit	1.3	W
Total Dissipation	PT	When mounted on ceramic substrate (900mm ² ×0.8mm)	1.4	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Package Dimensions

unit: mm (typ) 7045-006



Product & Package Information

• Package : EMH8

• JEITA, JEDEC : -

• Minimum Packing Quantity : 3,000 pcs./reel

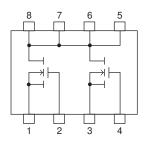
Taping Type: TL



Marking



Electrical Connection

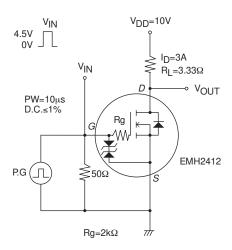


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Electrical Characteristics at Ta=25°C

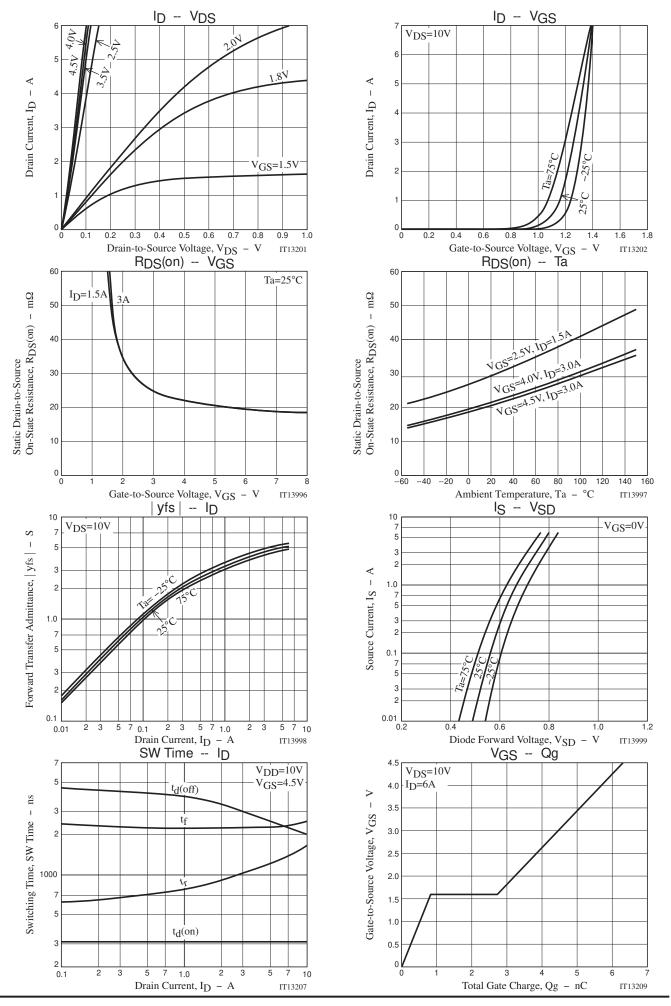
Parameter	Symbol	Conditions	Ratings			Unit	
Farameter	Syllibol	Conditions	min	typ	max	Onit	
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	24			V	
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =20V, V _{GS} =0V			-1	μΑ	
Gate-to-Source Leakage Current	IGSS	V _{GS} =±8V, V _{DS} =0V			±10	μΑ	
Cutoff Voltage	VGS(off)	V _{DS} =10V, I _D =1mA	0.5		1.3	٧	
Forward Transfer Admittance	yfs	V _{DS} =10V, I _D =3A	2.8	4.8		S	
	R _{DS} (on)1	I _D =3A, V _{GS} =4.5V	16	21	27	mΩ	
Static Drain to Source On State Begintance	R _{DS} (on)2	I _D =3A, V _{GS} =4V	17	22	29	mΩ	
Static Drain-to-Source On-State Resistance	R _{DS} (on)3	I _D =3A, V _{GS} =3.1V	18	25	34	mΩ	
	RDS(on)4	ID=1.5A, VGS=2.5V	21	30	42	mΩ	
Turn-ON Delay Time	t _d (on)			310		ns	
Rise Time	t _r	See an edified Test Circuit		1020		ns	
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.		3000		ns	
Fall Time	tf			2250		ns	
Total Gate Charge	Qg			6.3		nC	
Gate-to-Source Charge	Qgs	V _{DS} =10V, V _{GS} =4.5V, I _D =6A		0.83		nC	
Gate-to-Drain "Miller" Charge	Qgd			1.9		nC	
Diode Forward Voltage	V _{SD}	I _S =6A, V _{GS} =0V		0.8	1.2	V	

Switching Time Test Circuit

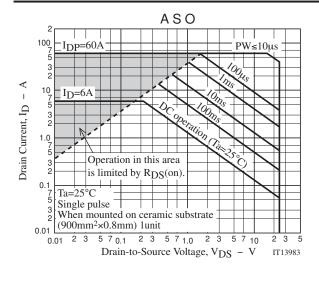


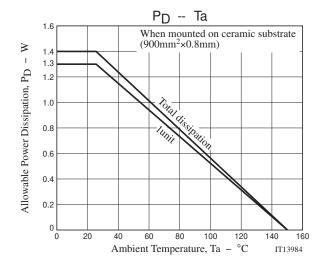
Ordering Information

Device	Package	Shipping	memo	
EMH2412-TL-H	MH2412-TL-H EMH8		Pb Free and Halogen Free	



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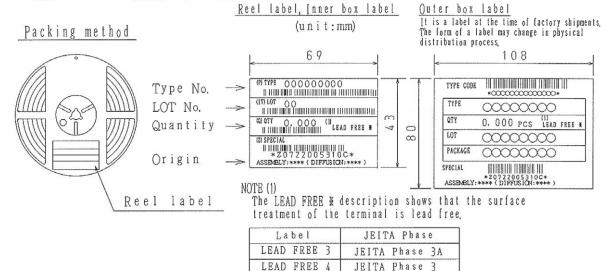


Embossed Taping Specification

EMH2412-TL-H

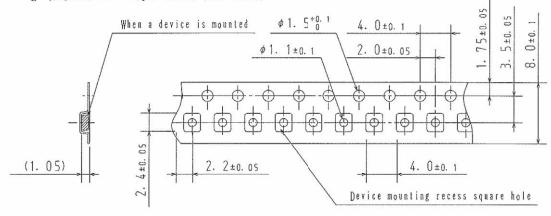
1. Packing Format

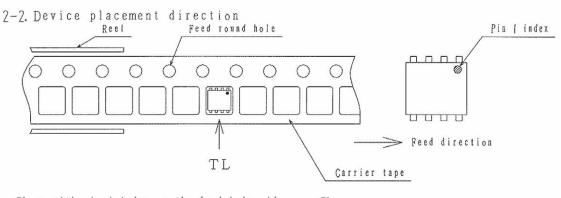
Package Name Carrier Tape		Maximum Number of devices contained (pcs)			Packing format		
	Type	Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)	
EMH8	MCP4	3, 000	15, 000	90,000		6 inner boxes contained	
					Dimensions:mm (external)	Dimensions:mm (external)	
					183×72×185	440×195×210	



2. Taping configuration

7-1. Carrier tape size (unit:mm)



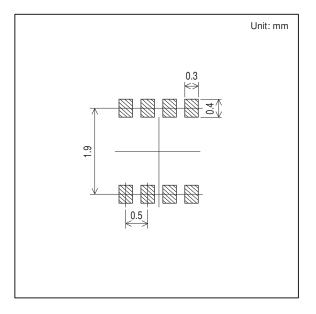


Outline Drawing

EMH2412-TL-H

Mass (g) Unit 0.008 mm 2.0:a.04 8 7 6 5 10 11 25 0.05 10 11 25

Land Pattern Example



Note on usage: Since the EMH2412 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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